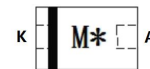


**WSB5546N**
**0.2A, Schottky Barrier Diode**
[Http://www.sh-willsemi.com](http://www.sh-willsemi.com)
**Features**

- Low reverse current
- 0.2A Average rectified forward current
- Standard products are Pb-free and Halogen-free


**DFN1006-2L**

**Circuit**

**Marking**
**Absolute maximum ratings**

Parameter	Symbol	Value	Unit
Reverse voltage (repetitive peak)	$V_{RM}$	40	V
Reverse voltage (DC)	$V_R$	40	V
Average rectified forward current	$I_O$	0.2	A
Peak forward current <sup>(1)</sup>	$I_{FSM}$	3	A
Junction temperature	$T_J$	150	°C
Operating temperature	$T_{opr}$	-40 ~ 150	°C
Storage temperature	$T_{stg}$	-55 ~ 150	°C

**Electronics characteristics ( $T_A=25^{\circ}C$ )**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward voltage <sup>(2)</sup>	$V_F$	$I_F=0.2A$	-	0.51	0.60	V
Reverse current	$I_R$	$V_R=10V$	-	-	0.5	uA
		$V_R=40V$	-	-	1	uA
Junction capacitance	$C_J$	$V_R=4V, F=1MHz$	-	17	-	pF
Thermal resistance	$R_{\theta(j-a)}$	Junction to ambient	-	-	500	K/W

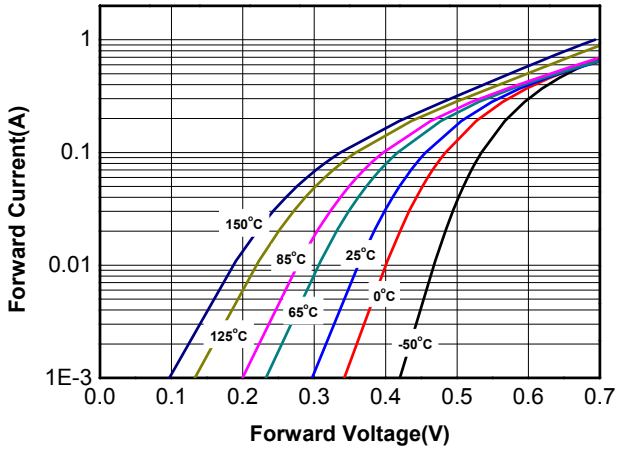
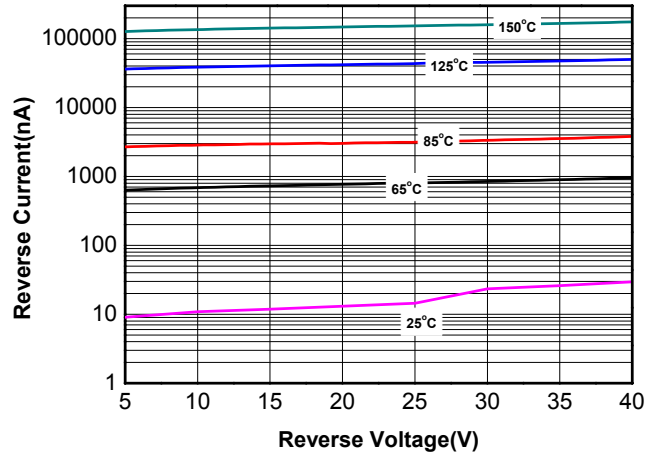
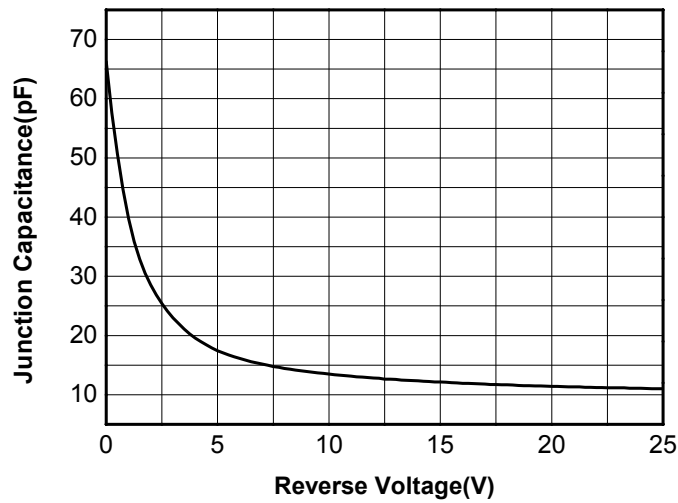
**Order Informations**

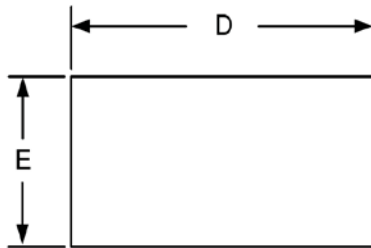
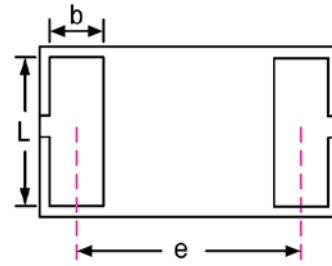
Device	Package	Marking	Shipping
WSB5546N-2/TR	DFN1006-2L	M* <sup>(3)</sup>	10000/Reel&Tape

**Note 1:** Pulse Width=8.3ms, Single half-sine Pulse;

**Note 2:** Pulse Width<380us;

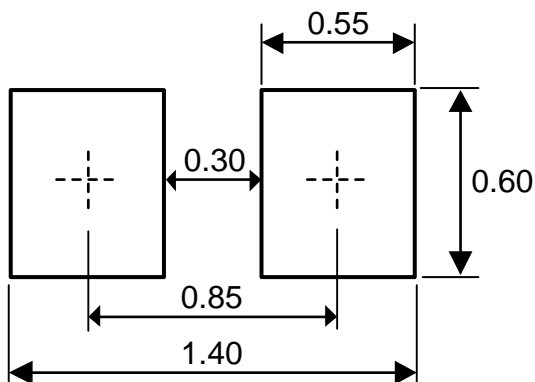
**Note 3:**\* = Month code (A~Z); M = Device code;

**Typical characteristics (Ta=25°C, unless otherwise noted)**

**Forward voltage vs. Forward current**

**Reverse current vs. Reverse voltage**

**Junction capacitance vs. Reverse voltage**

**Package outline dimensions**
**DFN1006-2L**

**Top View**

**Bottom View**

**Side View**

Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	0.40	-	0.50
A1	0.00	-	0.05
A3	0.125 Ref.		
D	0.95	1.00	1.05
E	0.55	0.60	0.65
b	0.20	0.25	0.30
L	0.45	0.50	0.55
e	0.65 Typ.		

**Recommend land pattern (Unit: mm)**

**Notes:**

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met.